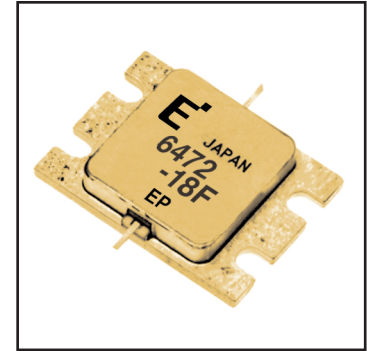


FEATURES

- High Output Power: $P_{1dB} = 43.0\text{dBm}$ (Typ.)
- High Gain: $G_{1dB} = 9.5\text{dB}$ (Typ.)
- High PAE: $\eta_{add} = 37\%$ (Typ.)
- Low $IM_3 = -46\text{dBc}$ @ $P_o = 32.0\text{dBm}$
- Broad Band: 6.4 ~ 7.2GHz
- Impedance Matched $Z_{in}/Z_{out} = 50\Omega$
- Hermetically Sealed Package



DESCRIPTION

The FLM6472-18F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

Eudyna's stringent Quality Assurance Program assures the highest reliability and consistent performance.

ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25^\circ\text{C}$)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		15	V
Gate-Source Voltage	V_{GS}		-5	V
Total Power Dissipation	P_T	$T_C = 25^\circ\text{C}$	83.3	W
Storage Temperature	T_{stg}		-65 to +175	$^\circ\text{C}$
Channel Temperature	T_{ch}		175	$^\circ\text{C}$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 48.0 and -8.4 mA respectively with gate resistance of 25 Ω .

ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25^\circ\text{C}$)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	I_{DSS}	$V_{DS} = 5\text{V}, V_{GS} = 0\text{V}$	-	7.5	11.25	A
Transconductance	g_m	$V_{DS} = 5\text{V}, I_{DS} = 4875\text{mA}$	-	7500	-	mS
Pinch-off Voltage	V_p	$V_{DS} = 5\text{V}, I_{DS} = 250\text{mA}$	-0.5	-1.5	-3.0	V
Gate Source Breakdown Voltage	V_{GSO}	$I_{GS} = -250\mu\text{A}$	-5.0	-	-	V
Output Power at 1dB G.C.P.	P_{1dB}	$V_{DS} = 10\text{V},$ $I_{DS} = 0.65 I_{DSS}$ (Typ.), $f = 6.4 \sim 7.2 \text{GHz},$ $Z_S = Z_L = 50 \text{ohm}$	42.0	43.0	-	dBm
Power Gain at 1dB G.C.P.	G_{1dB}		8.5	9.5	-	dB
Drain Current	I_{dsr}		-	4875	6000	mA
Power-added Efficiency	η_{add}		-	37	-	%
Gain Flatness	ΔG		-	-	± 0.6	dB
3rd Order Intermodulation Distortion	IM_3	$f = 7.2 \text{GHz}, \Delta f = 10 \text{MHz}$ 2-Tone Test $P_{out} = 32.0\text{dBm}$ S.C.L.	-44	-46	-	dBc
Thermal Resistance	R_{th}	Channel to Case	-	1.6	1.8	$^\circ\text{C}/\text{W}$
Channel Temperature Rise	ΔT_{ch}	$10\text{V} \times I_{dsr} \times R_{th}$	-	-	80	$^\circ\text{C}$

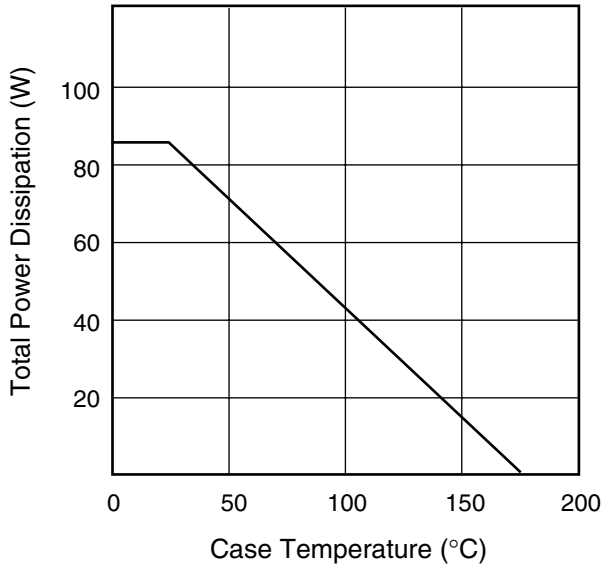
CASE STYLE: IK

G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

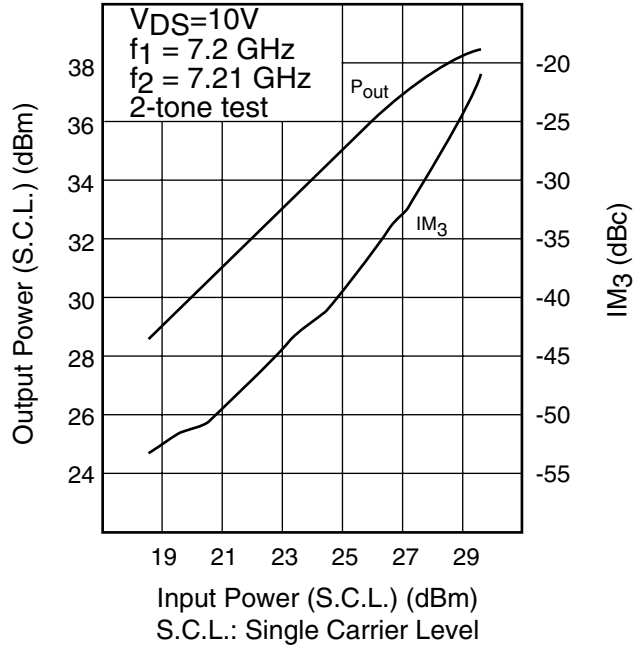
FLM6472-18F

C-Band Internally Matched FET

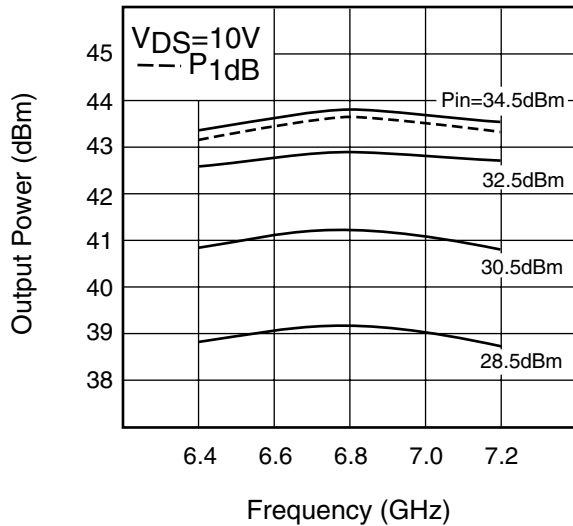
POWER DERATING CURVE



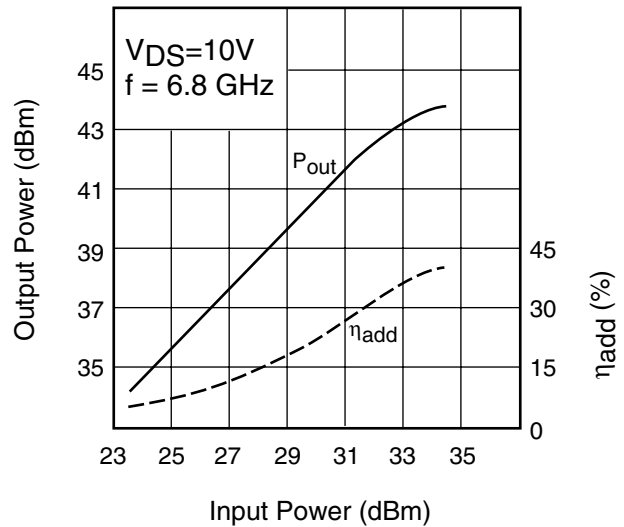
OUTPUT POWER & IM₃ vs. INPUT POWER

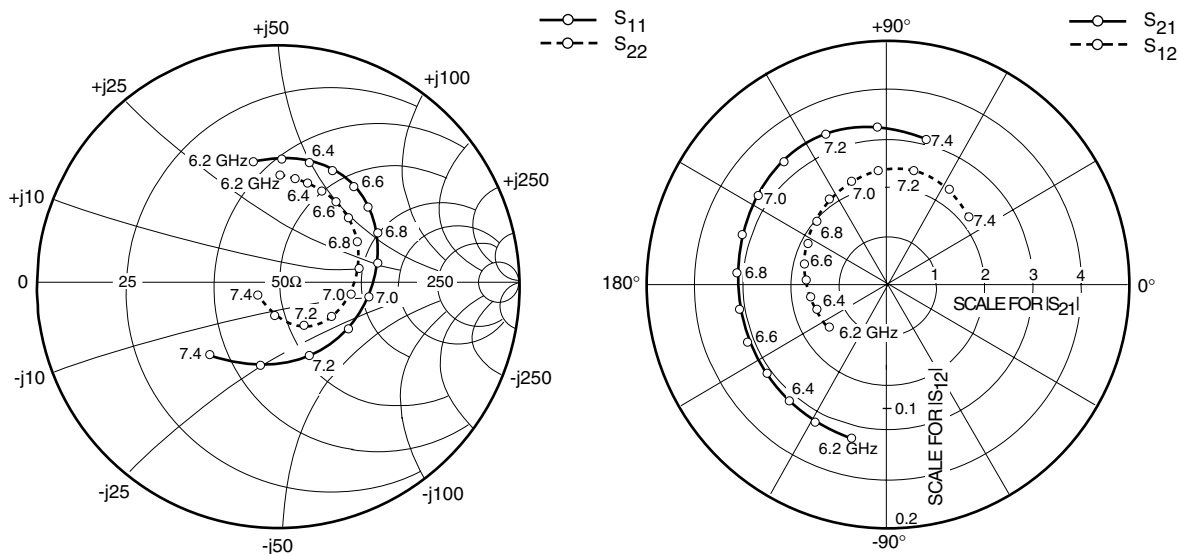


OUTPUT POWER vs. FREQUENCY



OUTPUT POWER vs. INPUT POWER





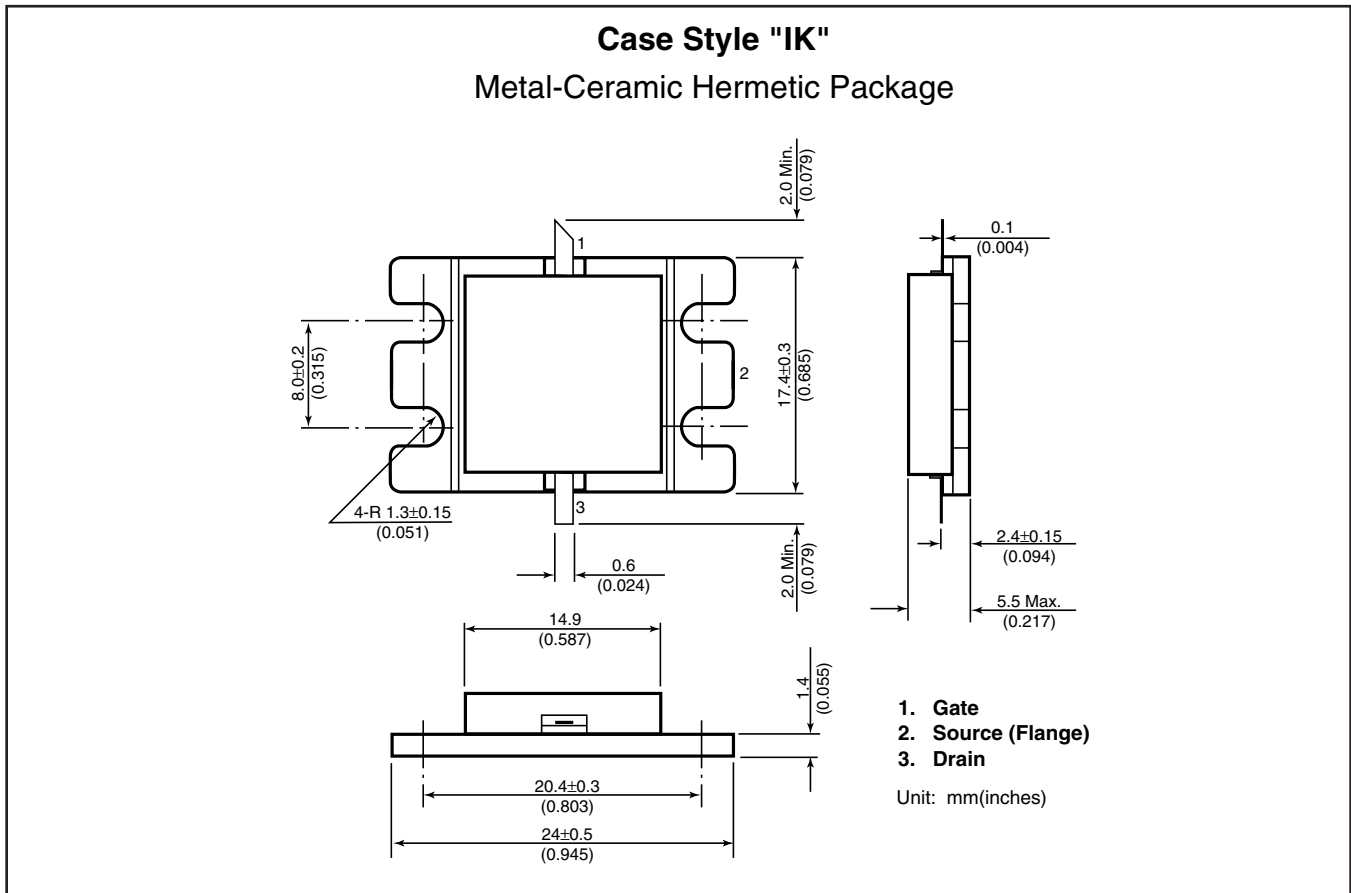
S-PARAMETERS

$V_{DS} = 10V, I_{DS} = 4875mA$

FREQUENCY (MHZ)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
6200	.517	101.5	3.232	-103.7	.062	-144.7	.453	89.3
6300	.521	88.0	3.197	-118.5	.064	-159.2	.445	81.8
6400	.524	75.7	3.135	-130.9	.066	-170.7	.432	74.0
6500	.519	64.3	3.075	-144.6	.068	-176.9	.424	65.8
6600	.507	52.6	3.108	-158.3	.071	164.6	.410	55.5
6700	.490	40.7	3.111	-171.2	.074	152.8	.391	43.5
6800	.463	27.1	3.149	175.1	.079	139.3	.369	28.7
6900	.426	11.1	3.226	160.5	.086	125.2	.339	11.3
7000	.385	-9.3	3.308	145.2	.090	110.1	.301	-9.4
7100	.345	-33.6	3.366	129.9	.094	95.4	.259	-31.8
7200	.326	-66.5	3.378	112.2	.096	77.0	.202	-59.4
7300	.349	-102.2	3.287	93.9	.092	57.5	.141	-95.5
7400	.411	-134.0	3.133	75.3	.087	39.6	.098	-149.0

FLM6472-18F

C-Band Internally Matched FET



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CAUTION

Eudyna Devices Inc. products contain **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put this product into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

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